

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known		
			Application Number	10/698,501	
			Filing Date	October 31, 2003	
			First Named Inventor	Heon Lee	
			Art Unit	2824	
			Examiner Name	Son T. Dinh	
Sheet	C1	of	C1	Attorney Docket Number	5649-2226

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code (if known)			
	1	US- 2003/0198113 A1	10-23-2003	Abraham et al.	
	2	US- 2003/0123282 A1	07-03-2003	Nickel et al.	
	3	US- 6,535,416 B1	03-18-2003	Daughton et al.	
	4	US- 2003/0073398 A1	01-09-2003	Daughton et al.	
	5	US- 6,385,082 B1	05-07-2002	Abraham et al.	

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Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code, Number, Kind Code (if known)				
	6	CN 1365117 A	08-21-2002	Hewlett Packard Development Co.		T
	7	DE 10 2004 022 573 A1	04-07-2005	Hewlett Packard Development Co.		T
	8	DE 10 2004 029 060 A1	05-12-2005	Hewlett Packard Development Co.		T
	9	DE 10 2004 030 587 A1	06-02-2005	Hewlett Packard Development Co.		T
	10	DE 17 74 058 C3	11-25-71	Centre National de la Recherche Scientifique		T
	11	FR 2 832 542 A1	05-23-2003	Commissariat Energie Atomique		T
	12	JP 04-023293 A	01-27-1992	Toshiba Corp.		T

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	13	Beech et al., "Curie point written magnetoresistive memory," Journal of Applied Physics, Vol. 87, No. 9, May 1, 2000, pp. 6403-6405	
	14	Daughton et al., "Design of Curie point written magnetoresistance random access memory cells," Journal of Applied Physics, Vol. 93, No. 10, May 15, 2003, pp. 7304-7306	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.